

P-Channel Enhancement Mode Field Effect Transistor

General Description

The CMSA60P06 uses advanced technology to provide excellent $R_{DS(on)}$. This device is suitable to be used as the low side FET in SMPS, load switching and general purpose.

Features

- Simple Drive Requirement
- Lower On-resistance
- 100% EAS Guaranteed
- RoHS Compliant

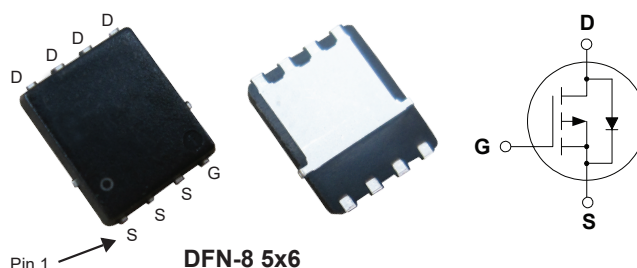
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
-60V	20mΩ	-40A

Applications

- Load Switch
- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA60P06	DFN-8 5*6	CMSA60P06

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	-40	A
I_{DM}	Pulsed Drain Current	-120	A
EAS	Single Pulse Avalanche Energy ¹	240	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	45	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient	---	44.6	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case	---	2.78	$^\circ\text{C/W}$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-20A$	---	---	20	m Ω
		$V_{GS}=-4.5V$, $I_D=-15A$	---	---	24	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1	---	-3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-60V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-10A$	---	26	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	60	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-48V$, $I_D=-40A$ $V_{GS}=-10V$	---	91	---	nC
Q_{gs}	Gate-Source Charge		---	17	---	
Q_{gd}	Gate-Drain Charge		---	29	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V$, $V_{GS}=-10V$, $R_L=1.5\Omega$ $I_D=-20A$	---	21	---	ns
T_r	Rise Time		---	11	---	
$T_{d(off)}$	Turn-Off Delay Time		---	200	---	
T_f	Fall Time		---	61	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4600	---	pF
C_{oss}	Output Capacitance		---	250	---	
C_{rss}	Reverse Transfer Capacitance		---	120	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-40	A
I_{SM}	Pulsed Source Current		---	---	-120	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=-20A$	---	-0.86	-1.2	V

Note :

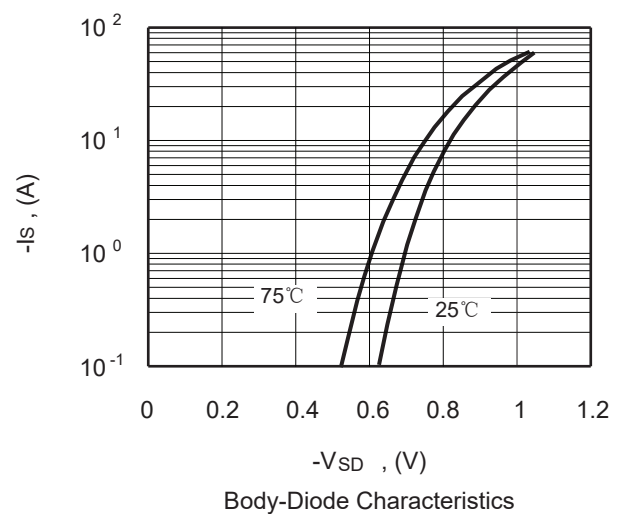
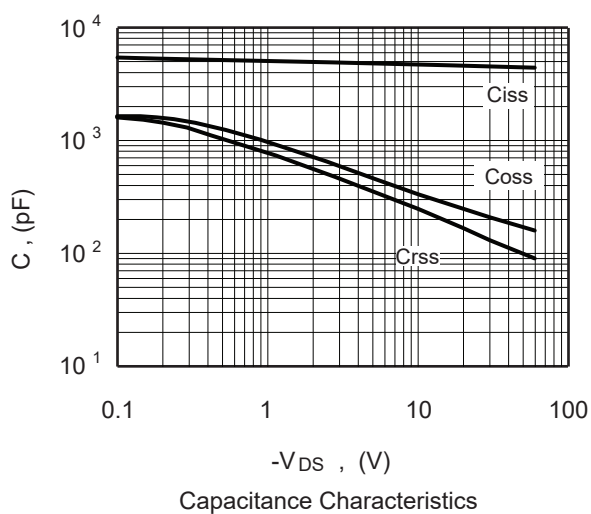
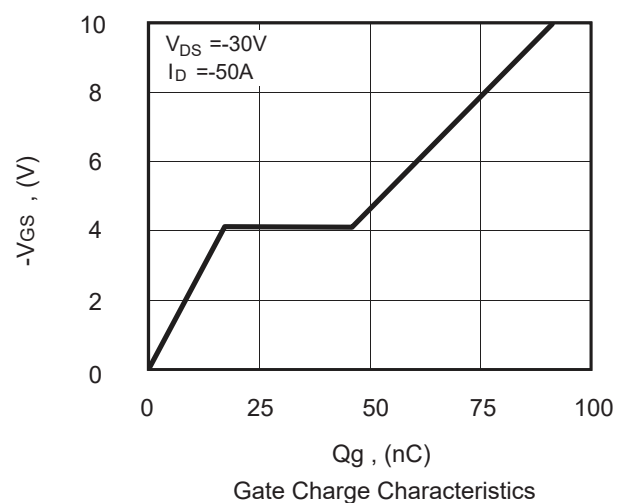
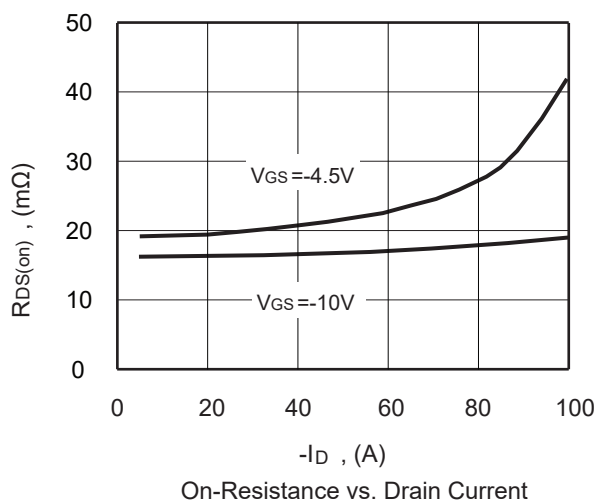
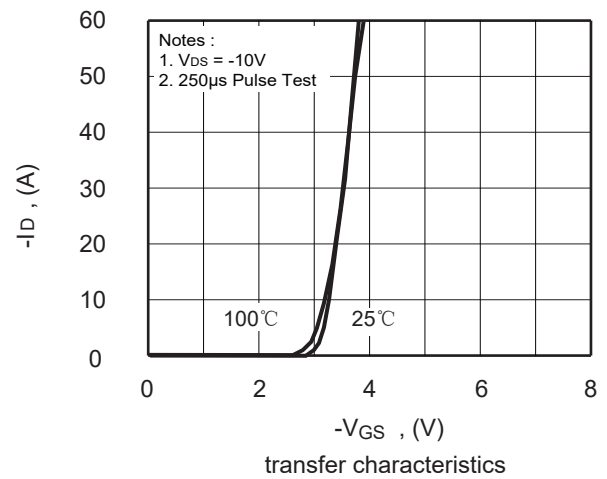
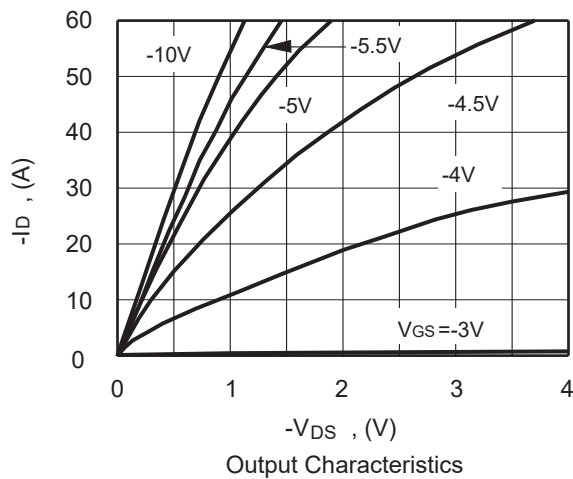
1.The test condition is $V_{DD}=30V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_D=31A$

This product has been designed and qualified for the consumer market.

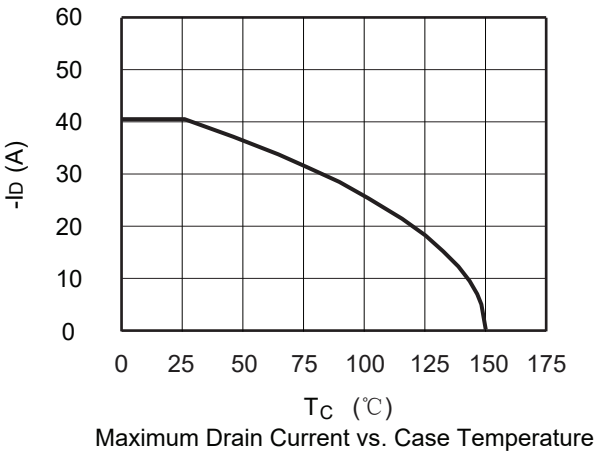
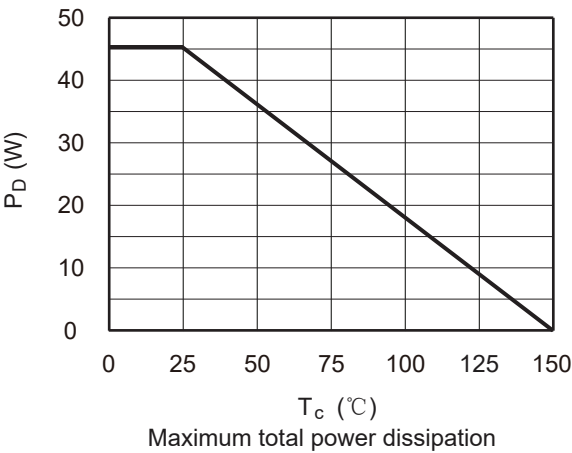
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Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

Typical Characteristics



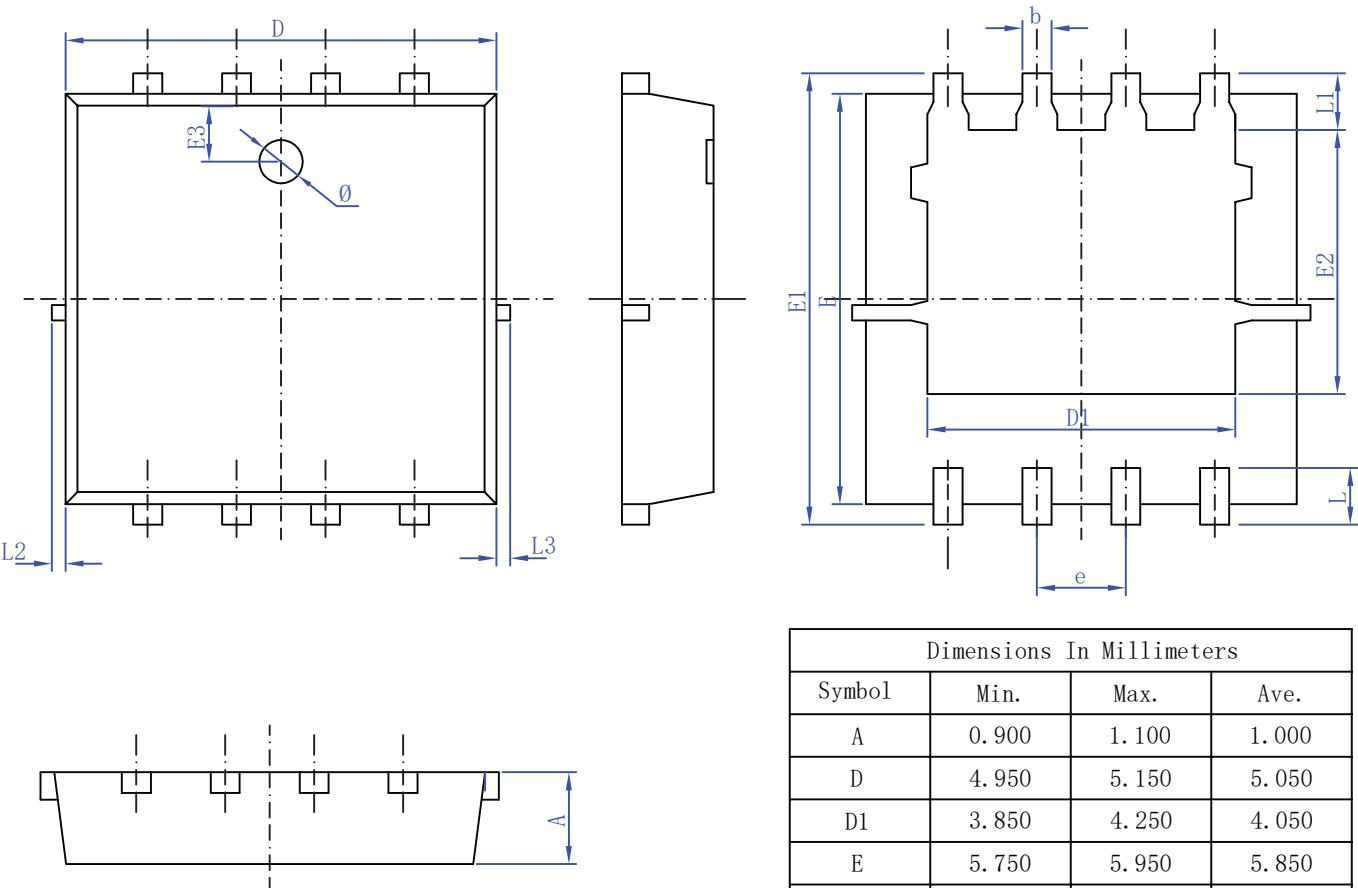
Typical Characteristics



Package Dimension

DFN-8 5x6

Unit :mm



注：
1. 未注公差±0.05未标注圆角R_{max}=0.25

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.900	1.100	1.000
D	4.950	5.150	5.050
D1	3.850	4.250	4.050
E	5.750	5.950	5.850
E1	5.950	6.350	6.150
E2	3.300	3.700	3.500
E3	0.900	1.300	1.100
b	0.250	0.350	0.300
e	1.220	1.320	1.270
L	0.585	0.785	0.685
L1	0.525	0.725	0.625
Ø	1.000	1.400	1.200
L2	0~0.100		
L3	0~0.100		